

# PJQ5546S6V-AU

## 40V N-Channel Enhancement Mode MOSFET

**Voltage**

**40 V**

**Current**

**67 A**

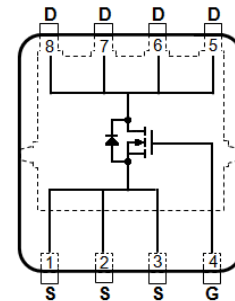
### Features

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@20A < 6.2m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@7V$ ,  $I_D@10A < 9.3m\Omega$
- Excellent FOM
- Standard Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case : DFN5060-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.08 grams

DFN5060-8L



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>(Note 3)</sup>	$T_C=25^\circ\text{C}$	$I_D$	67	A
	$T_C=100^\circ\text{C}$		47	
Pulsed Drain Current <sup>(Note 1)</sup>	$T_C=25^\circ\text{C}$	$I_{DM}$	240	
Power Dissipation	$T_C=25^\circ\text{C}$	$P_D$	50	W
	$T_C=100^\circ\text{C}$		25	
Continuous Drain Current <sup>(Note 4)</sup>	$T_A=25^\circ\text{C}$	$I_D$	17.3	A
	$T_A=70^\circ\text{C}$		14.5	
Power Dissipation	$T_A=25^\circ\text{C}$	$P_D$	3.3	W
	$T_A=70^\circ\text{C}$		2.3	
Single Pulse Avalanche Current <sup>(Note 5)</sup>		$I_{AS}$	10.5	A
Single Pulse Avalanche Energy <sup>(Note 5)</sup>		$E_{AS}$	50	mJ
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~175	$^\circ\text{C}$
Thermal Resistance <sup>(Note 4)</sup>	Junction to Case	$R_{\theta JC}$	3	$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$	45	

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## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	3	4	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	5	6.2	mΩ
		V <sub>GS</sub> =7V, I <sub>D</sub> =10A	-	7.1	9.3	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Dynamic <sup>(Note 6)</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =32V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	16.3	25	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	4.8	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	-	792	1200	pF
Output Capacitance	C <sub>oss</sub>		-	284	430	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	23	42	
Gate resistance	R <sub>g</sub>	f=1MHz	-	1.1	-	Ω
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DS</sub> =32V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω (Note 2)	-	7.7	-	ns
Turn-On Rise Time	tr		-	4.3	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	16	-	
Turn-Off Fall Time	tf		-	6	-	
Drain-Source Diode						
Diode Forward Current	Is	T <sub>C</sub> =25° C (Package Limit)	-	-	57	A
Pulsed Diode Forward Current	ISM		-	-	240	
Diode Forward Voltage	VSD	Is=20A, VGS=0V	-	0.8	1.3	V
Reverse Recovery Time	Trr	VDD=32V, VGS=0V,	-	19	-	ns
Reverse Recovery Charge	Qrr	Is=20A, dIs/dt=100A/us	-	6	-	nC

### NOTES :

1. Pulse width ≤ 100us, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature typical characteristics.
3. Chip capability with an R<sub>θJC</sub>=3°C/W.
4. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
5. E<sub>AS</sub> is calculated based on the condition of L=1mH, I<sub>AS</sub>=10A, V<sub>DD</sub>=30V, V<sub>GS</sub>=10V. 100% test at L=0.5mH, I<sub>AS</sub>=10.5A in production.
6. Guaranteed by design, not subject to production testing.

# PJQ5546S6V-AU

## TYPICAL CHARACTERISTIC CURVES

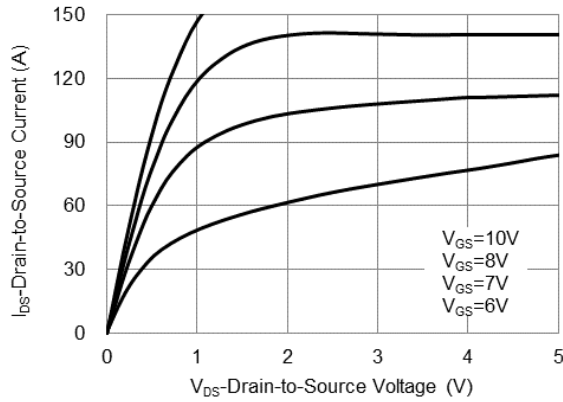


Fig.1 On-Region Characteristics

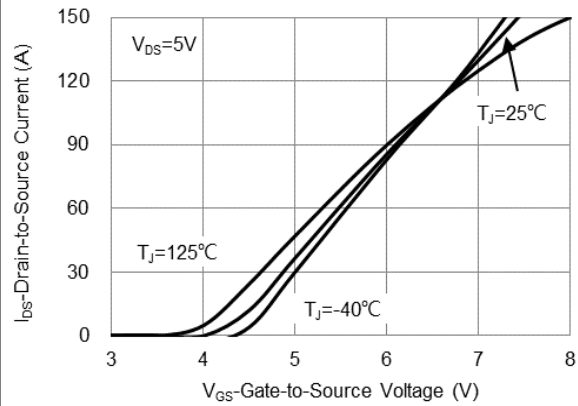


Fig.2 Transfer Characteristics

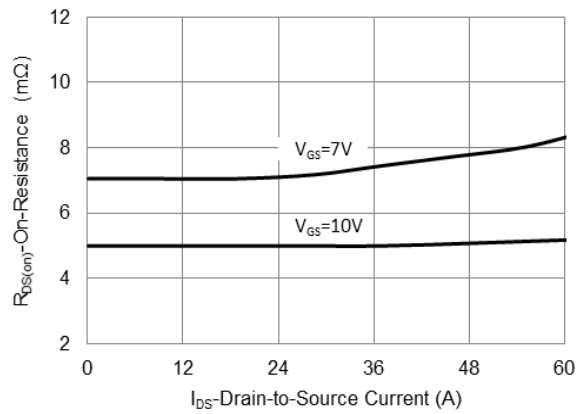


Fig.3 On-Resistance vs. Drain Current

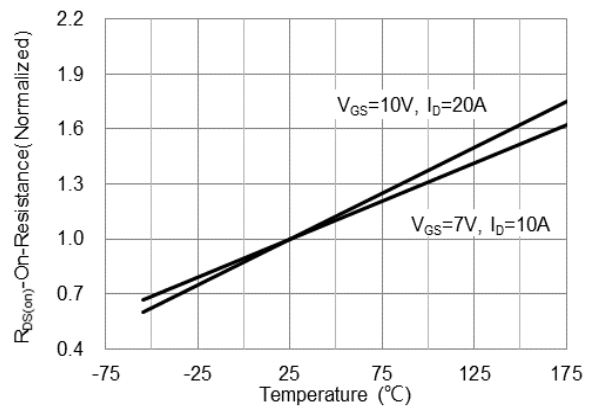


Fig.4 On-Resistance vs. Junction temperature

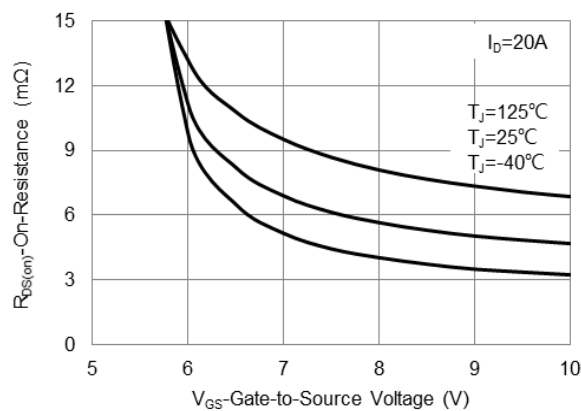


Fig.5 On-Resistance Variation with  $V_{GS}$

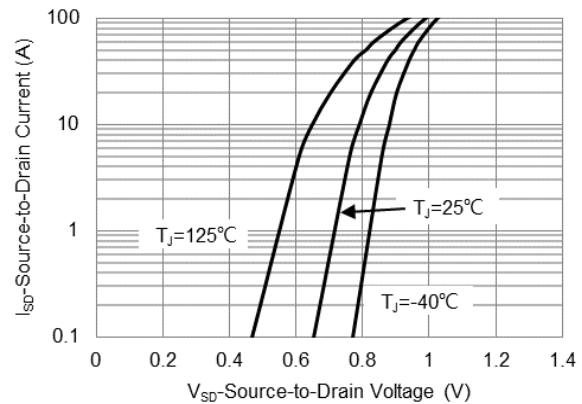
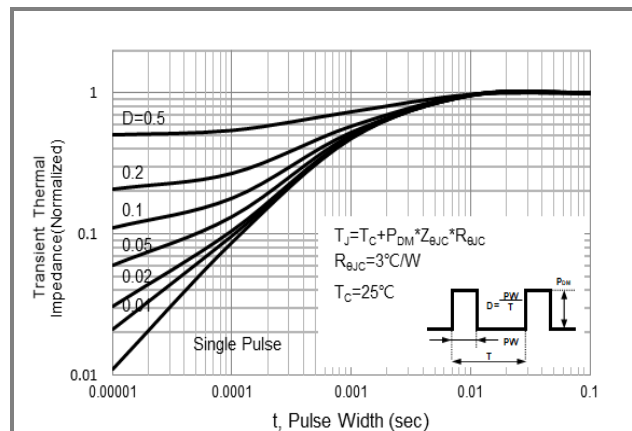
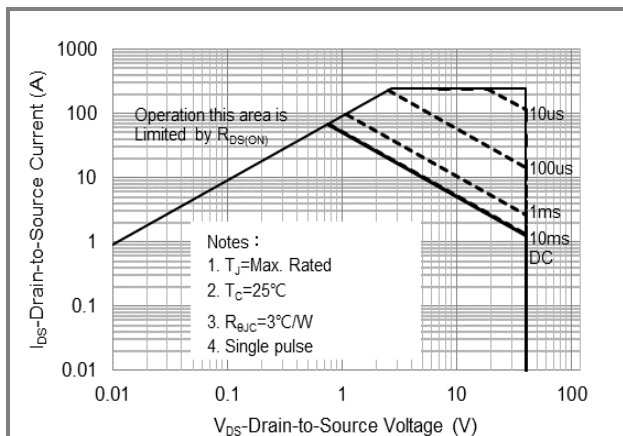
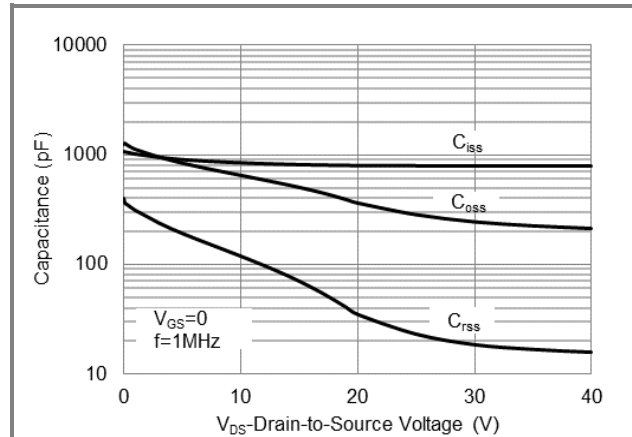
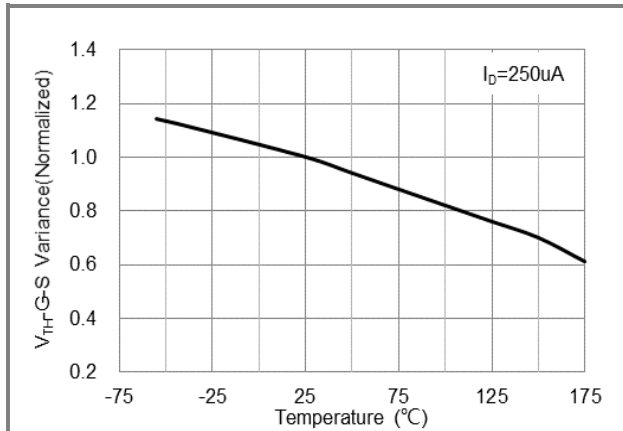
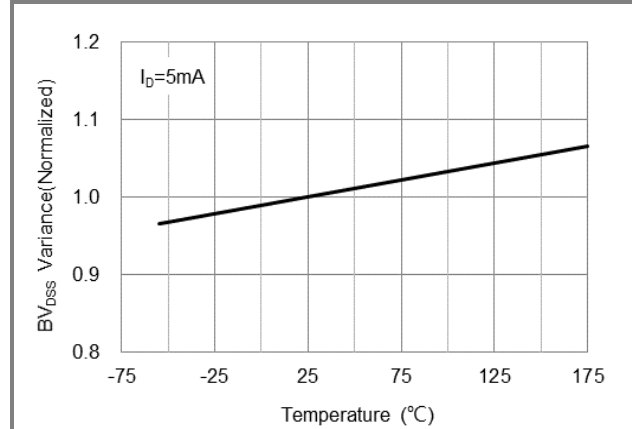
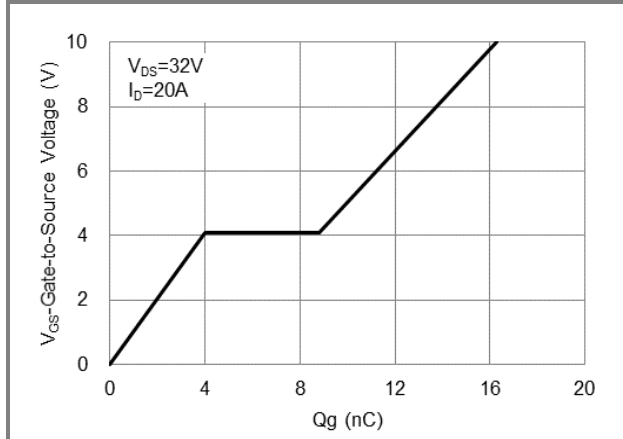


Fig.6 Source-Drain Diode Forward Voltage

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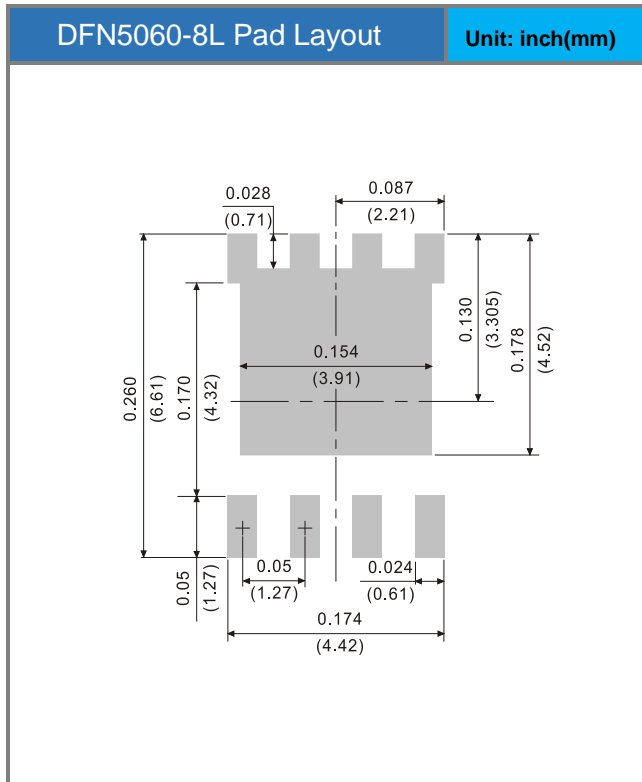
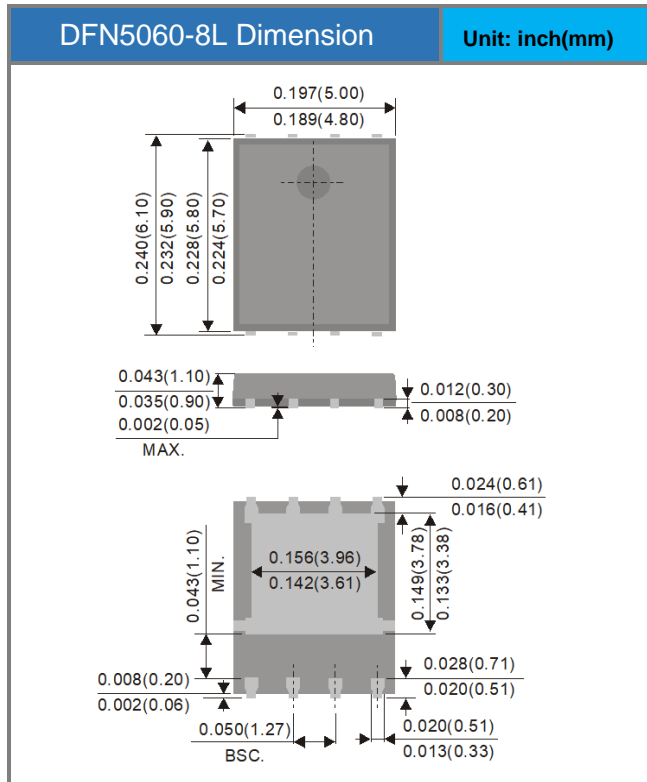


# PJQ5546S6V-AU

## Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ5546S6V-AU	DFN5060-8L	3K pcs / 13" reel	5546S6V

## Packaging Information & Mounting Pad Layout



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